

ABSTRACT

It is disclosed an over-coating agent for forming fine patterns which is applied to cover a substrate having thereon photoresist patterns and allowed to shrink under heat so that the spacing between adjacent photoresist patterns is lessened, with the applied film of the over-coating agent being removed substantially completely to form or define fine trace patterns, further characterized by containing either a water-soluble polymer and an amide group-containing monomer or a water-soluble polymer which contains at least (meth)acrylamide as a monomeric component. Also disclosed is a method of forming fine-line patterns using any one of said over-coating agents. According to the invention, the thermal shrinkage of the over-coating agent for forming fine patterns in the heat treatment can be extensively increased, and one can obtain fine-line patterns which exhibit good profiles while satisfying the characteristics required of semiconductor devices.